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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Morito AKIYAMA et al.

Atty. Ref.: 1035-548

Serial No. 10/516,333

TC/A.U.: unassigned

Filed: November 30, 2004

Examiner: unassigned

For: PIEZOELECTRIC ELEMENT BASED ON SUPERHIGH-ORIENTED
ALUMINUM NITRIDE THIN FILM AND MANUFACTURING METHOD
THEREOF

* * * * *

January 4, 2005

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO-1449.

- All listed documents are attached.
- Copies of U.S. Patent Publications are not required and are not attached.
- Listed foreign patent publications and other documents are enclosed.
- The listed documents were cited in the ISR and copies should have been supplied by WIPO directly to the US PTO. If copies are not timely received from WIPO, please telephone the undersigned so that copies can be timely supplied for the Examiner's consideration in this US National Phase Application.

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

Respectfully submitted,

NIXON & VANDERHYE P.C.

By:



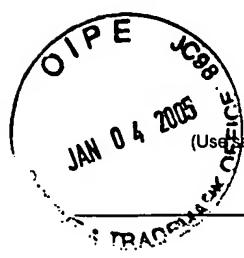
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INFORMATION DISCLOSURE CITATION		ATTY. DOCKET NO.	SERIAL NO.
		<u>1035-548</u>	<u>10/516,333</u>
		APPLICANT	
		<u>Morito AKIYAMA et al.</u>	
		FILING DATE	TC/A.U.
		<u>November 30, 2004</u>	<u>unassigned</u>
(Use several sheets if necessary)			



U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

	"Low-temperature growth of piezoelectric AlN film by rf reactive planar magnetron sputtering", T. Shiosaki et al., Appl. Phys. Lett. 36(8), 15 April 1980, 643-645, © 1980 American Institute of Physics
	"Structural and electroacoustic studies of AlN thin films during low temperature radio frequency sputter deposition", F. Engelmark et al., J. Vac. Sci. Technol. A19(5), Sep/Oct 2001, 2664-2669, © 2001 American Vacuum Society
	"Structural properties of AlN films grown on Si, Ru/Si and ZnO/Si substrates", Won Taeg Lim et al., Thin solid Films 382(2001) 56-60, © 2001 Elsevier Science
	"Synthesis and Surface Acoustic Wave Property of Aluminum Nitride Thin films Fabricated on Silicon and Diamond Substrates Using the Sputtering Method", M. Ishihara et al., Jpn. J. Appl. Phys, vol. 40(2001) pp. 5065-5068 Part 1, No. 8, August, © 2001 The Japan Society of Applied Physics
	"Deposition of AlN thin film using reactive sputtering method", Y. Honda et al., Reports of Kumamoto Industrial Research Institute No. 35, 1997, pp. 59-63 © Kumamoto Industrial Research Institute

***Examiner**

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.